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# FDMC8588DC

## N-Channel Dual Cool™ 33 PowerTrench® MOSFET 25 V, 40 A, 5.7 mΩ

### Features

- Dual Cool™ Top Side Cooling PQFN package
- Max  $r_{DS(on)} = 5.7\text{ m}\Omega$  at  $V_{GS} = 4.5\text{ V}$ ,  $I_D = 17\text{ A}$
- State-of-the-art switching performance
- Lower output capacitance, gate resistance, and gate charge boost efficiency
- Shielded gate technology reduces switch node ringing and increases immunity to EMI and cross conduction
- RoHS Compliant

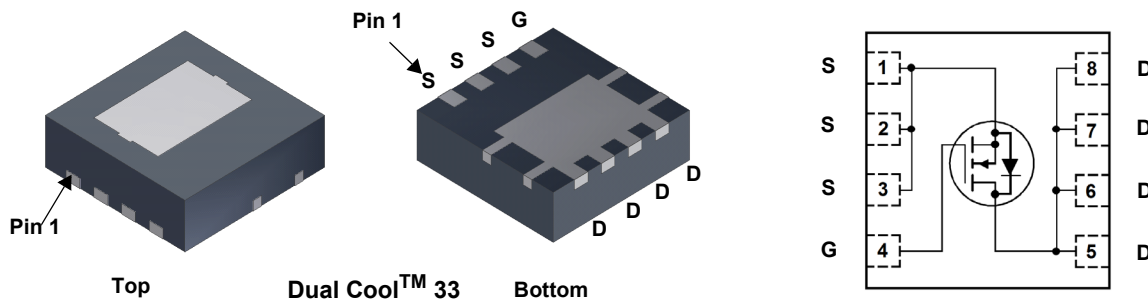


### General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $r_{DS(on)}$ , fast switching speed and body diode reverse recovery performance.

### Applications

- High side switching for high end computing
- High power density DC-DC synchronous buck converter



### MOSFET Maximum Ratings $T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Notes	Rated Values	Units
$V_{DS}$	Drain to Source Voltage	(Note 5)	25	V
$V_{GS}$	Gate to Source Voltage	(Note 4)	$\pm 12$	V
$I_D$	Drain Current - Continuous (Package limited) $T_C = 25\text{ }^\circ\text{C}$		40	A
	- Continuous (Silicon Limited) $T_C = 25\text{ }^\circ\text{C}$		73	
	- Continuous	(Note 1a)	17	
	- Pulsed		60	
$E_{AS}$	Single Pulse Avalanche Energy	(Note 3)	29	mJ
$P_D$	Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	41	W
	Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$ (Note 1a)	3.0	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range		-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Top Source)	7.0	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Bottom Drain)	3.0	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	42	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	105	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1i)	17	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1j)	26	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1k)	12	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
08DC	FDMC8588DC	Dual Cool™ 33	13"	12 mm	3000 units

**Electrical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$	25			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		5		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 20\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current, Forward	$V_{GS} = 12\text{ V}$ , $V_{DS} = 0\text{ V}$			100	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$	0.8	1.2	1.8	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		-4		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 18\text{ A}$		3.6	5.0	m $\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 17\text{ A}$		4.1	5.7	
		$V_{GS} = 10\text{ V}$ , $I_D = 18\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$		5.5	7.6	
$g_{FS}$	Forward Transconductance	$V_{DD} = 5\text{ V}$ , $I_D = 17\text{ A}$		103		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 13\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$		1695		pF
$C_{oss}$	Output Capacitance			493		pF
$C_{rss}$	Reverse Transfer Capacitance			63		pF
$R_g$	Gate Resistance			0.4		$\Omega$

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 13\text{ V}$ , $I_D = 17\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$		8		ns
$t_r$	Rise Time			3		ns
$t_{d(off)}$	Turn-Off Delay Time			25		ns
$t_f$	Fall Time			2		ns
$Q_{g(TOT)}$	Total Gate Charge at 4.5V			12		nC
$Q_{gs}$	Total Gate Charge	$V_{DD} = 13\text{ V}$ , $I_D = 17\text{ A}$		3.0		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			3.0		nC

**Drain-Source Diode Characteristics**

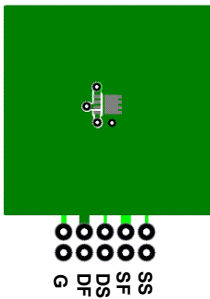
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 2\text{ A}$ (Note 2)		0.7	1.2	V
		$V_{GS} = 0\text{ V}$ , $I_S = 17\text{ A}$ (Note 2)		0.8	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F = 17\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		25		ns
$Q_{rr}$	Reverse Recovery Charge			10		nC

## Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case (Top Source)	7.0	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Bottom Drain)	3.0	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	42	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	105	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1c)	29	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1d)	40	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1e)	19	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1f)	23	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1g)	30	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1h)	79	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1i)	17	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1j)	26	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1k)	12	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1l)	16	

### Notes:

- $R_{\theta JA}$  is determined with the device mounted on a 1in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a. 42 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b. 105 °C/W when mounted on a minimum pad of 2 oz copper

- Still air, 20.9x10.4x12.7mm Aluminum Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
- Still air, 20.9x10.4x12.7mm Aluminum Heat Sink, minimum pad of 2 oz copper
- Still air, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
- Still air, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper
- 200FPM Airflow, No Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
- 200FPM Airflow, No Heat Sink, minimum pad of 2 oz copper
- 200FPM Airflow, 20.9x10.4x12.7mm Aluminum Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
- 200FPM Airflow, 20.9x10.4x12.7mm Aluminum Heat Sink, minimum pad of 2 oz copper
- 200FPM Airflow, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in<sup>2</sup> pad of 2 oz copper
- 200FPM Airflow, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.

3.  $E_{AS}$  of 29 mJ is based on starting  $T_J = 25^{\circ}\text{C}$ ,  $L = 1.2\text{ mH}$ ,  $I_{AS} = 7\text{ A}$ ,  $V_{DD} = 23\text{ V}$ ,  $V_{GS} = 10\text{V}$ . 100% tested at  $L = 0.1\text{ mH}$ ,  $I_{AS} = 16\text{ A}$ .

4. As an N-ch device, the negative Vgs rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

5. The continuous Vds rating is 25V; however, a pulse of 28 V peak voltage for no longer than 3ns duration at 500KHz frequency can be applied.

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

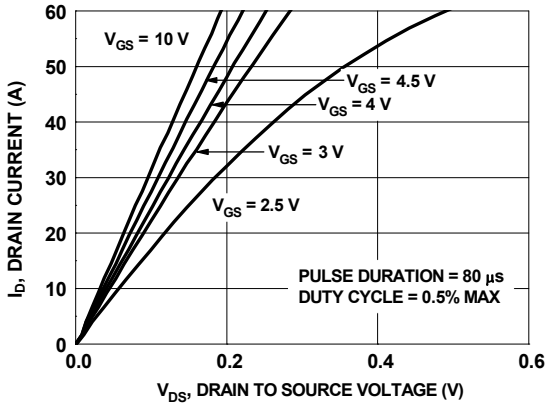


Figure 1. On Region Characteristics

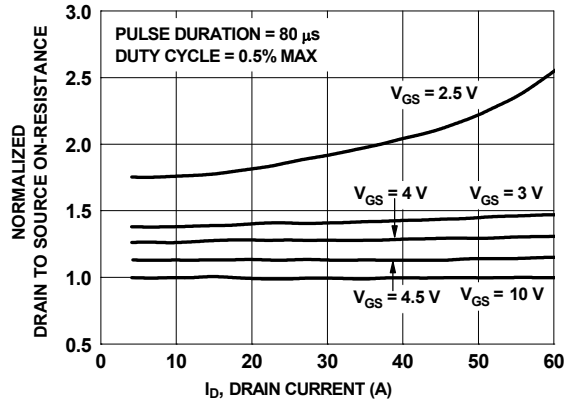


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

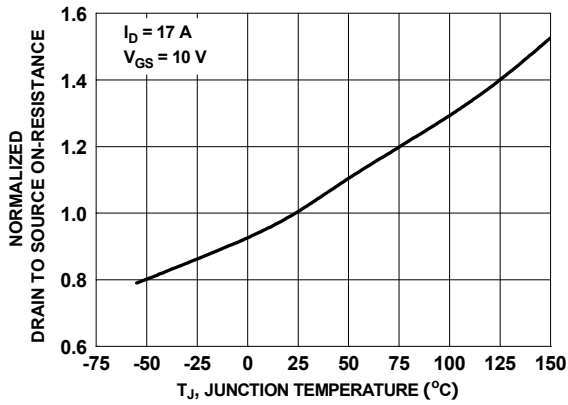


Figure 3. Normalized On Resistance vs Junction Temperature

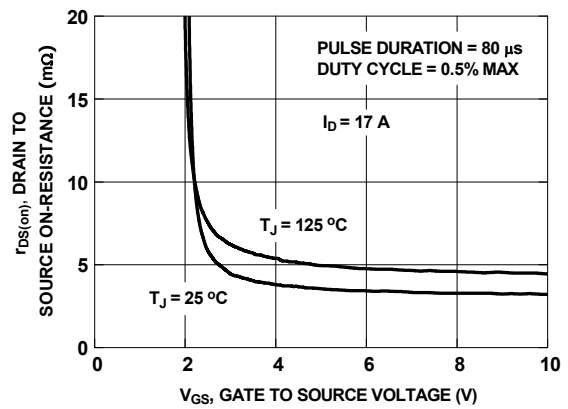


Figure 4. On-Resistance vs Gate to Source Voltage

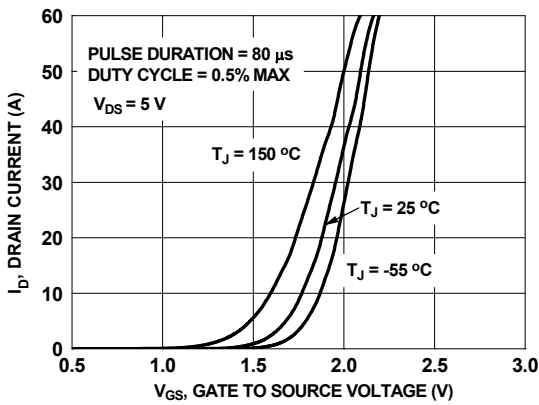


Figure 5. Transfer Characteristics

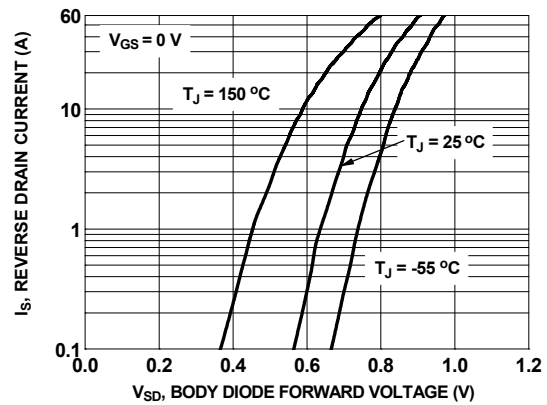
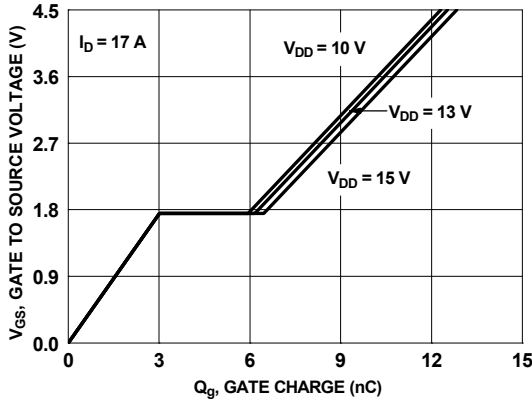
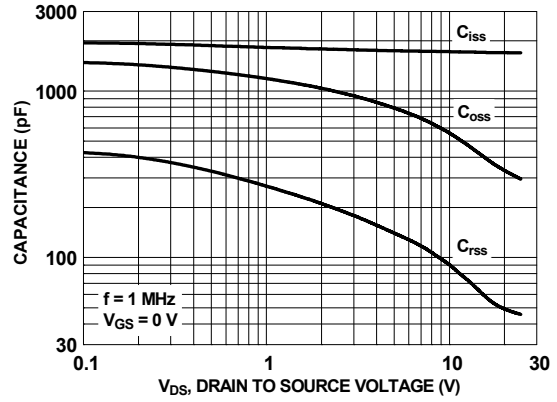


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

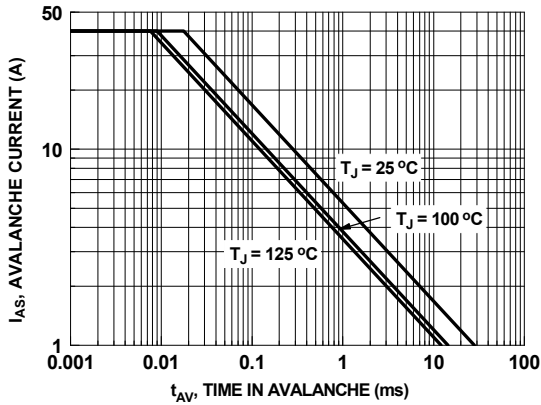
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



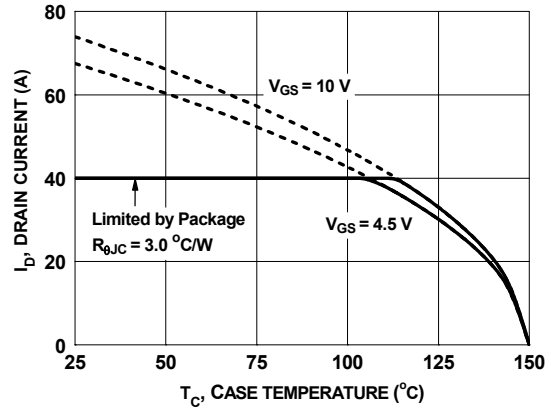
**Figure 7. Gate Charge Characteristics**



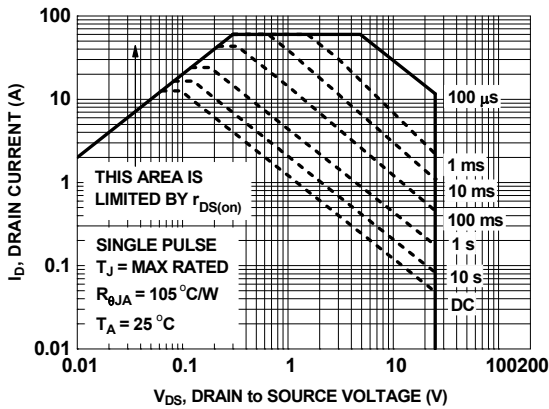
**Figure 8. Capacitance vs Drain to Source Voltage**



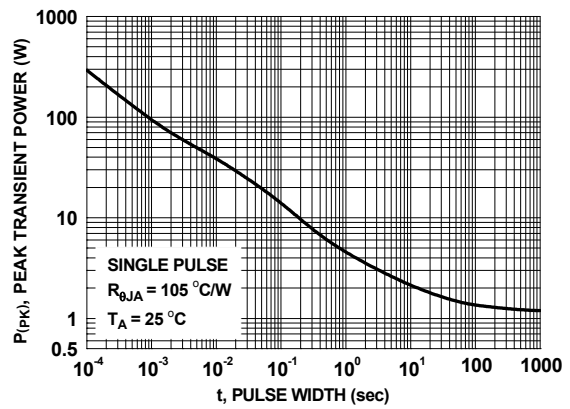
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs Case Temperature**

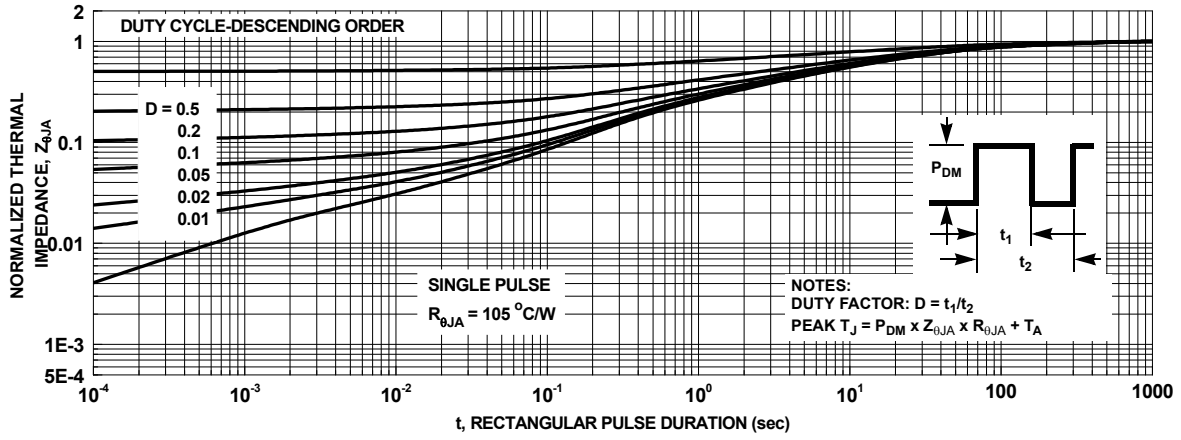


**Figure 11. Forward Bias Safe Operating Area**

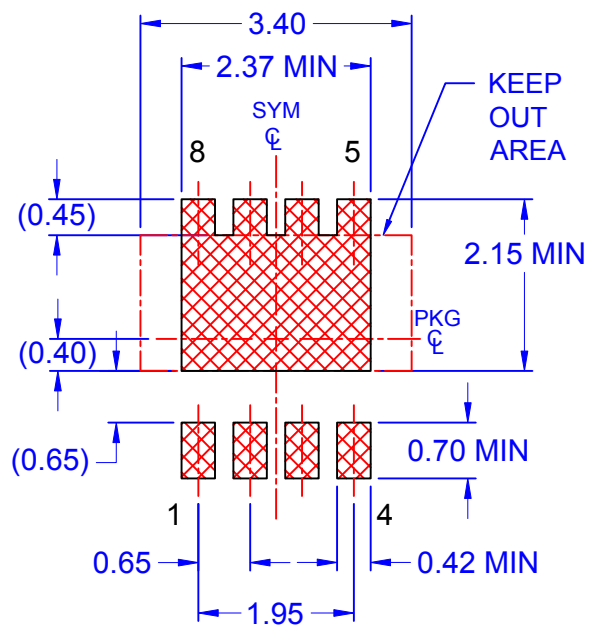
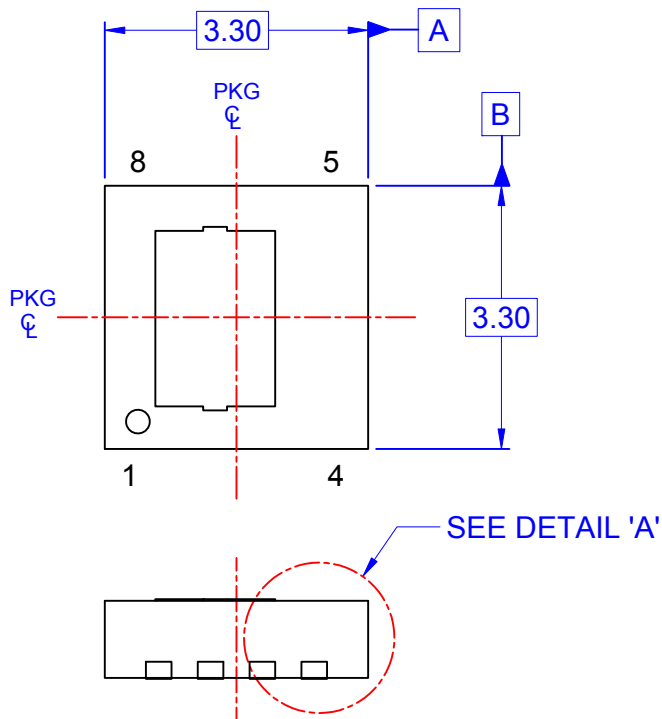


**Figure 12. Single Pulse Maximum Power Dissipation**

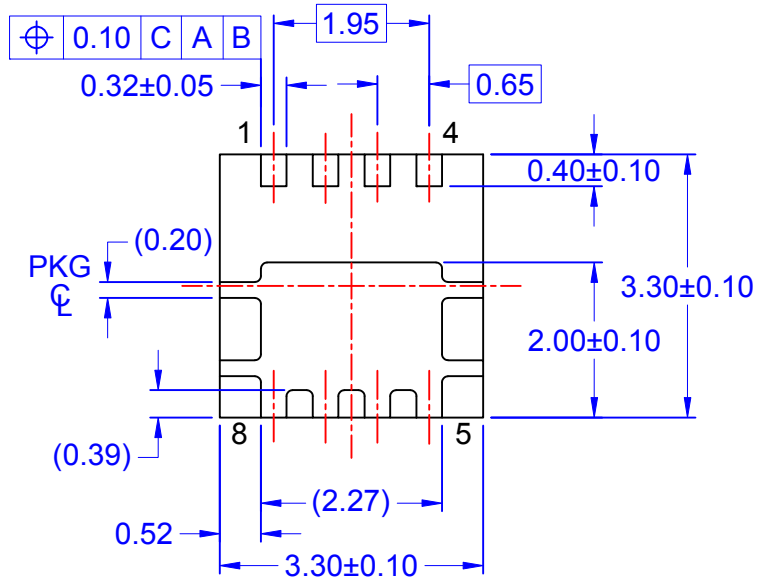
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



**Figure 13. Junction-to-Ambient Transient Thermal Response Curve**

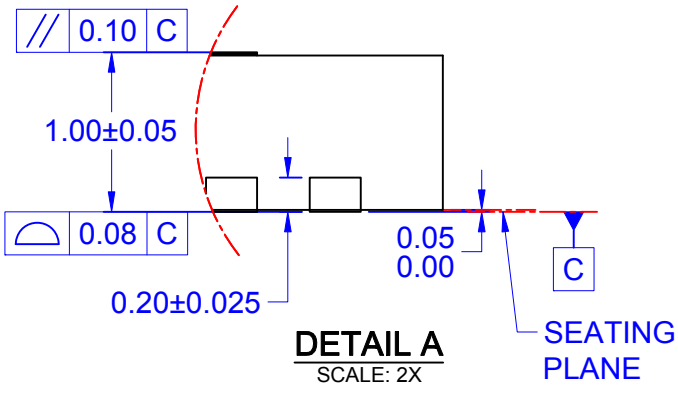


LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

- A) PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. BA, DATED OCTOBER 2002.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- E) DRAWING FILE NAME: PQFN08CREV3





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